

MM54C910/MM74C910 256 Bit TRI-STATE® Random Access Read/Write Memory

General Description

The MM54C910/MM74C910 is a 64 word by 4-bit random access memory. Inputs consist of six address lines, four data input lines, a \overline{WE} , and a \overline{ME} line. The six address lines are internally decoded to select one of the 64 word locations. An internal address register latches the address information on the positive to negative transition of $\overline{\text{ME}}$. The TRI-STATE outputs allow for easy memory expansion.

Address Operation: Address inputs must be stable (t_{SA}) prior to the positive to negative transition of $\overline{\text{ME}}$, and (t_{HA}) after the positive to negative transition of ME. The address register holds the information and stable address inputs are not needed at any other time.

Write Operation: Data is written into memory at the selected address if WE goes low while ME is low. WE must be held low for $t_{\overline{WE}}$ and data must remain stable t_{HD} after \overline{WE}

Read Operation: Data is nondestructively read from a memory location by an address operation with $\overline{\text{WE}}$ held Outputs are in the TRI-STATE (Hi-Z) condition when the device is writing or disabled.

Features

- Supply voltage range
- High noise immunity
- TTL compatible fan out
- Input address register
- Low power consumption
- 250 nW/package (typ.) (chip enabled or disabled)

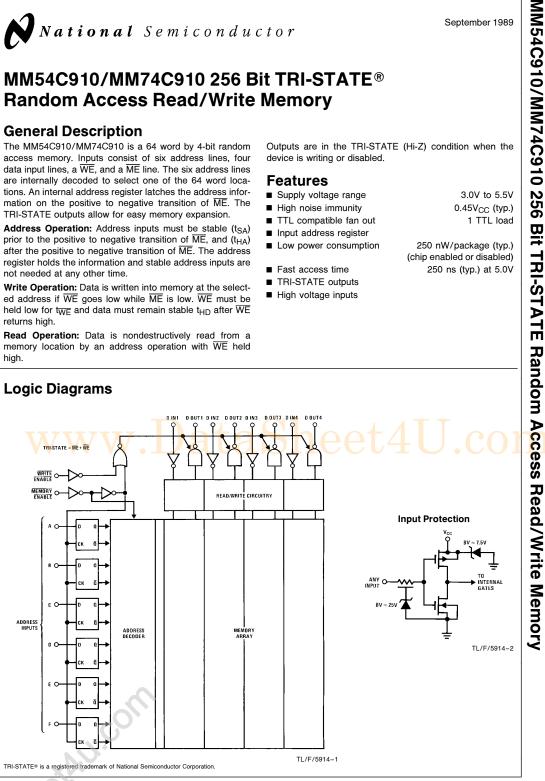
3.0V to 5.5V

0.45V_{CC} (typ.)

1 TTL load

- Fast access time 250 ns (typ.) at 5.0V
- TRI-STATE outputs
- High voltage inputs

Logic Diagrams



MMM 99182X

RRD-B30M105/Printed in U. S. A.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

 $\begin{array}{lll} \mbox{Voltage at Any Output Pin} & -0.3\mbox{V to V}_{\rm CC} + 0.3\mbox{V} \\ \mbox{Voltage at Any Input Pin} & -0.3\mbox{V to} + 15\mbox{V} \\ \end{array}$

 Power Dissipation
 700 mW

 Dual-In-Line
 700 mW

 Small Outline
 500 mW

 Operating V_{CC} Range
 3.0V to 5.5V

 Standby V_{CC} Range
 1.5V to 5.5V

Absolute Maximum (V_{CC}) Lead Temperature (T_L)

(Soldering, 10 sec.) 260°C

Operating Conditions

| poraumg coman | Min | Max | Units |
|-----------------------------------|------|------|-------|
| Supply Voltage (V _{CC}) | | | |
| MM54C910 | 4.5 | 5.5 | V |
| MM74C910 | 4.75 | 5.25 | V |
| Temperature (T _A) | | | |
| MM54C910 | -55 | +125 | °C |
| MM74C910 | -40 | +85 | °C |

DC Electrical Characteristics

Min/Max limits apply accross the temperature and power supply range indicated

| Symbol | Parameter | Conditions | Min | Тур | Max | Units |
|---------------------|---|---|-----------------------|----------------|------------|----------|
| V _{IN(1)} | Logical "1" Input Voltage | Full Range | V _{CC} - 1.5 | | | V |
| V _{IN(0)} | Logical "0" Input Voltage | Full Range | | | 0.8 | V |
| I _{IN(1)} | Logical "1" Input Current | $V_{IN} = 15V$ $V_{IN} = 5V$ | | 0.005 0.005 | 2.0 1.0 | μA μA |
| I _{IN(0)} | Logical "0" Input Current | $V_{IN} = 0V$ | -1.0 | -0.005 | | μΑ |
| V _{OUT(1)} | Logical "1" Output Voltage | $I_{O} = -150 \mu\text{A}$ $I_{O} = -400 \mu\text{A}$ | V _{CC} - 0.5 | | | V V |
| V _{OUT(0)} | Logical "0" Output Voltage | I _O = 1.6 mA | | | 0.4 | V |
| loz | Output Current in High Impedance State | $V_O = 5V$ $V_O = 0V$ | -1.0 | 0.005 0.005 | 1.0 | μA μA |
| Icc | Supply Current | $V_{CC} = 5V$ | | 5.0 | 300 | μΑ |

6.0V

AC Electrical Characteristics* $T_A = 25^{\circ}C$, $V_{CC} = 5.0V$, $C_L = 50$ pF

| Symbol | Parameter | Min | Тур | Max | Units |
|-----------------------------------|--|-----|-----|-----|-------|
| t _{ACC} | Access Time from Address | | 250 | 500 | ns |
| t _{pd} | Propagation Delay from ME | | 180 | 360 | ns |
| t _{SA} | Address Input Set-Up Time | 140 | 70 | | ns |
| t _{HA} | Address Input Hold Time | 20 | 10 | | ns |
| t _{ME} | Memory Enable Pulse Width | 200 | 100 | | ns |
| t _{ME} | Memory Enable Pulse Width | 400 | 200 | | ns |
| t _{SD} | Data Input Set-Up Time | 0 | | | ns |
| t _{HD} | Data Input Hold Time | 30 | 15 | | ns |
| tWE | Write Enable Pulse Width | 140 | 70 | | ns |
| t _{1H} , t _{0H} | Delay to TRI-STATE (Note 4) | | 100 | 200 | ns |
| ACITANCE | | | | | |
| C _{IN} | Input Capacity Any Input (Note 2) | | 5.0 | | pF |
| C _{OUT} | Output Capacity Any Output (Note 2) | | 9.0 | | pF |
| C _{PD} | Power Dissipation Capacity (Note 3) | | 350 | | pF |

AC Electrical Characteristics* (Continued) $T_A = 25$ °C, $V_{CC} = 5.0$ V, $C_L = 50$ pF

| Symbol | Parameter | MM54C910 $T_A = -55^{\circ}C \text{ to } +125^{\circ}C \\ V_{CC} = 4.5V \text{ to } 5.5V$ | | $\begin{aligned} \text{MM74C910} \\ \mathbf{T_A} &= -40^{\circ}\text{C to } + 85^{\circ}\text{C} \\ \mathbf{V_{CC}} &= 4.75\text{V to } 5.25\text{V} \end{aligned}$ | | Units |
|-------------------------------------|-----------------------------|---|-----|---|-----|-------|
| | | Min | Max | Min | Max | |
| t _{ACC} | Access Time from Address | | 860 | | 700 | ns |
| t _{pd1} , t _{pd0} | Propagation Delay from ME | | 660 | | 540 | ns |
| t _{SA} | Address Input Set-Up Time | 200 | | 160 | | ns |
| t _{HA} | Address Input Hold Time | 20 | | 20 | | ns |
| t _{ME} | Memory Enable Pulse Width | 280 | | 260 | | ns |
| t₩E | Memory Enable Pulse Width | 750 | | 600 | | ns |
| t _{SD} | Data Input Set-Up Time | 0 | | 0 | | ns |
| t _{HD} | Data Input Hold Time | 50 | | 50 | | ns |
| tWE | Write Enable Pulse Width | 200 | | 180 | | ns |
| t _{1H} , t _{0H} | Delay to TRI-STATE (Note 4) | | 200 | | 200 | ns |

^{*}AC Parameters are guaranteed by DC correlated testing.

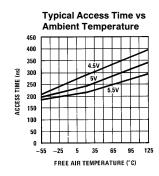
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Capacitance is guaranteed by periodic testing.

Note 3: C_{PD} determines the no load AC power consumption for any CMOS device. For complete explanation see 54C/74C Family Characteristics application note AN-90.

Note 4: See AC test circuits for t_{1H} , t_{0H} .

Typical Performance Characteristics

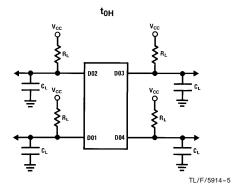


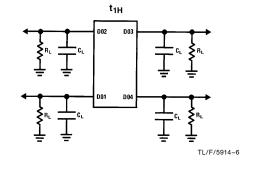
TL/F/5914-4

Truth Table

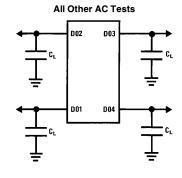
| ME | WE | Operation | Outputs |
|----|----|----------------|-----------|
| L | L | Write | TRI-STATE |
| L | Н | Read | Data |
| Н | L | Inhibit, Store | TRI-STATE |
| Н | Н | Inhibit, Store | TRI-STATE |

AC Test Circuits



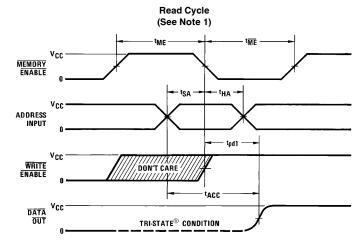


AC Test Circuits (Continued)

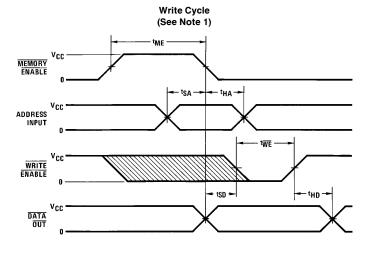


TL/F/5914-7

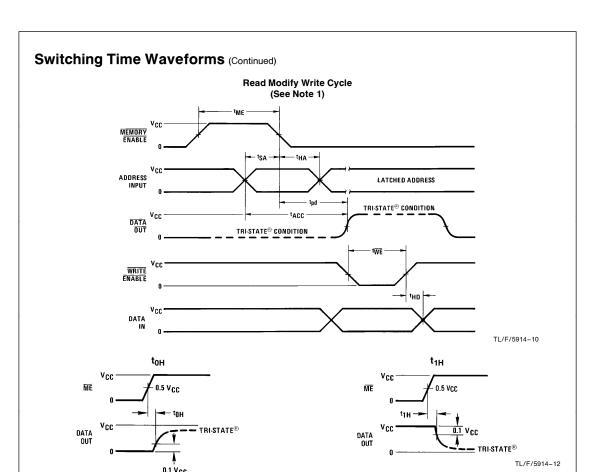
Switching Time Waveforms



TL/F/5914-8



TL/F/5914-9

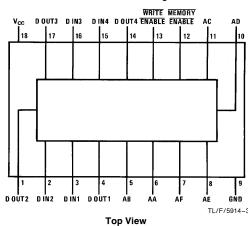


TL/F/5914-11

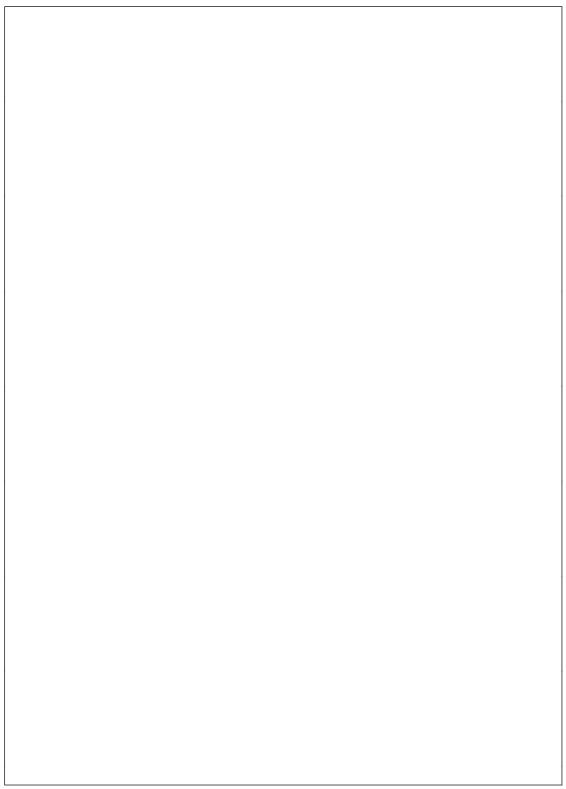
Note 1: $\overline{\text{MEMORY}}$ $\overline{\text{ENABLE}}$ must be brought high for t_{ME} nanoseconds between every address change. Note 2: $t_r = t_f = 20$ ns for all inputs.

Connection Diagram

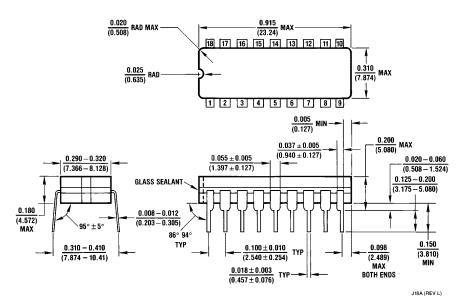
Dual-In-Line Package



Order Number MM54C910 or MM74C910

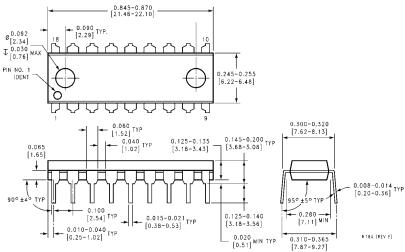






Ceramic Dual-In-Line Package (J) Order Number MM54C910J or MM74C910J NS Package Number J18A

Physical Dimensions inches (millimeters) (Continued)



Molded Dual-In-Line Package (N) Order Number MM54C910N or MM74C910N NS Package Number N18A

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